

**Multifunctional oriented nanocrystalline $\text{Pb}_{0.91}\text{La}_{0.06}\text{Zr}_{0.8}\text{Ti}_{0.2}\text{O}_3$ relaxor
ferroelectric thin film for chip power and thermal management**

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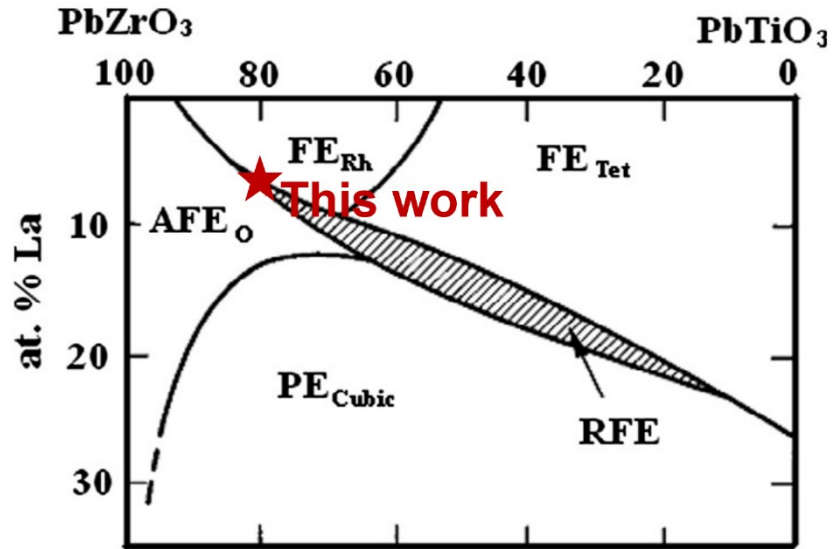


Fig. S1. The phase diagram of $(\text{PbLa})(\text{Zr,Ti})\text{O}_3$ system; the investigated composition in this work is located on the red star.

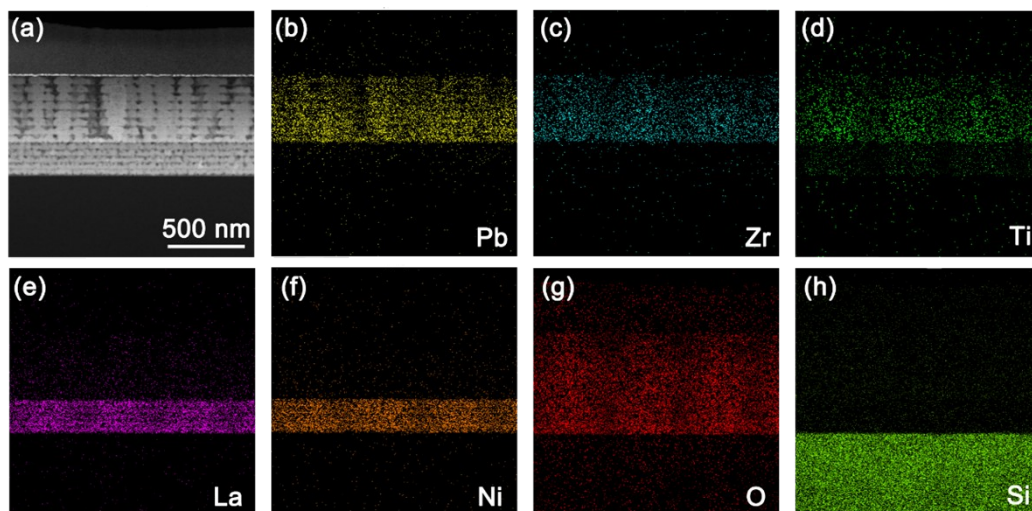


Fig. S2. (a) HAADF-STEM image and (b-h) elemental distribution mapping of the PLZT/LNO/Si thin film.

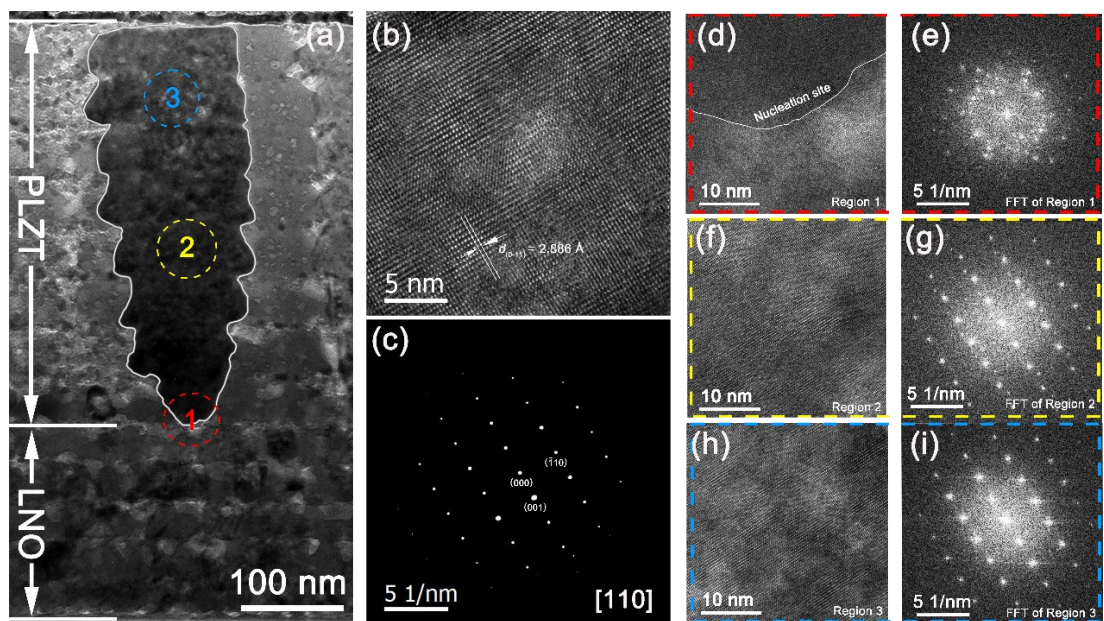


Fig. S3. (110)-oriented grain structure of the PLZT 6/80/20 thin film. (a) [110] direction grain morphology (inside the white solid line); (b) HRTEM atomic image and (c) SAED patterns of the grain viewing from the [110] direction; (d-i) separately show the morphology and corresponding FFT images of region 1, 2 and 3 inside the grain of (a).

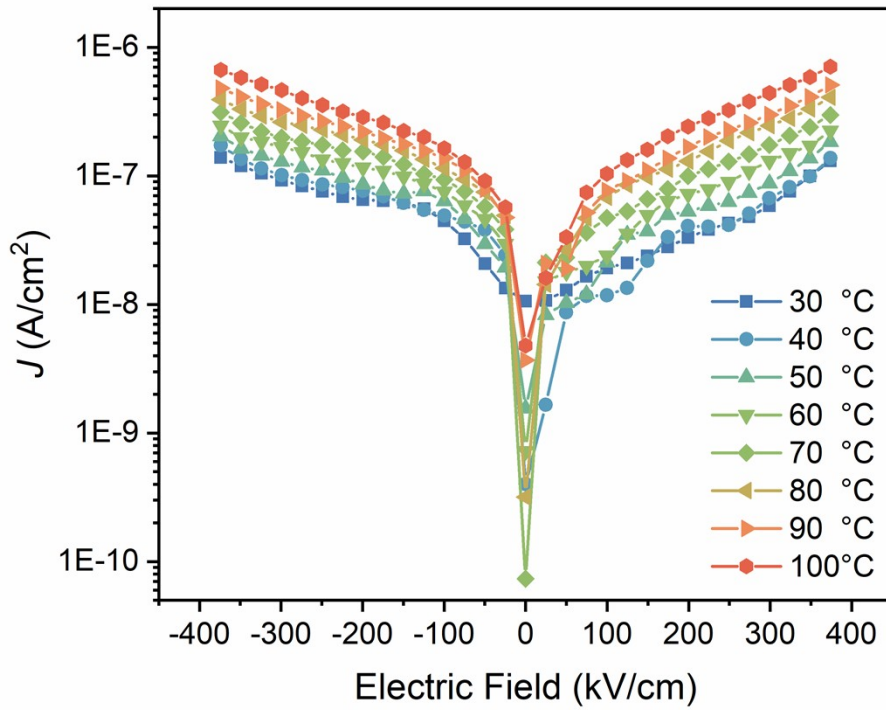


Fig. S4. The leakage current density-electric field (J - E) plots of the PLZT 6/80/20 film measured under different temperatures

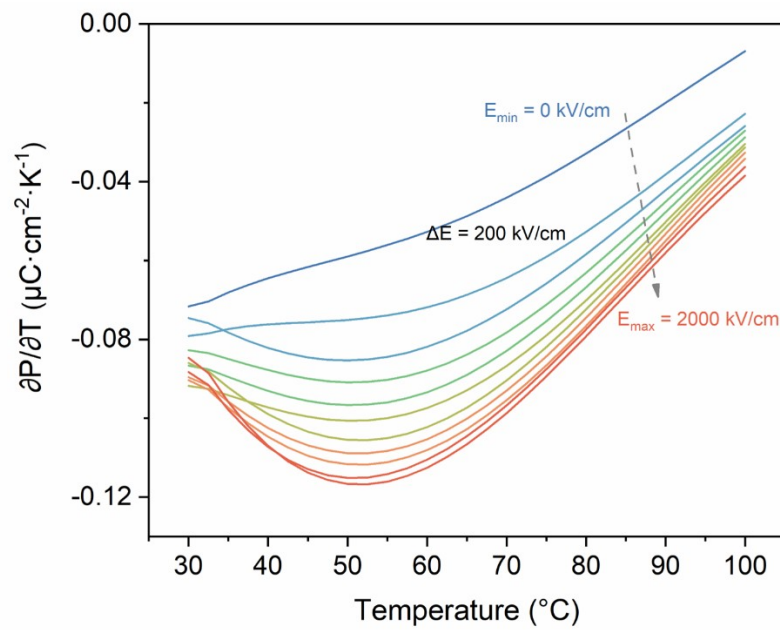


Fig. S5. $\partial P/\partial T$ obtained from six-order polynomial fitting of raw P - T data

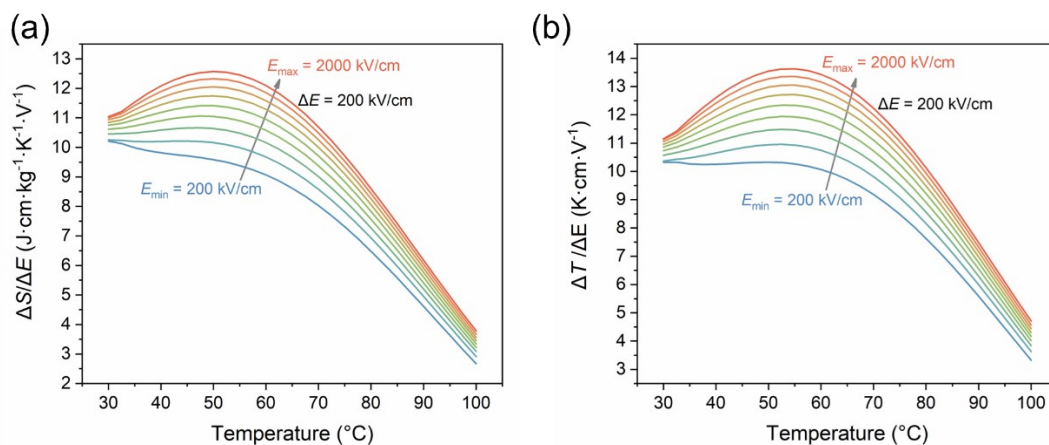


Fig. S6. Electrocaloric strength of the PLZT 6/80/20 thin film. (a) isothermal entropy change strength and (b) adiabatic temperature change strength.

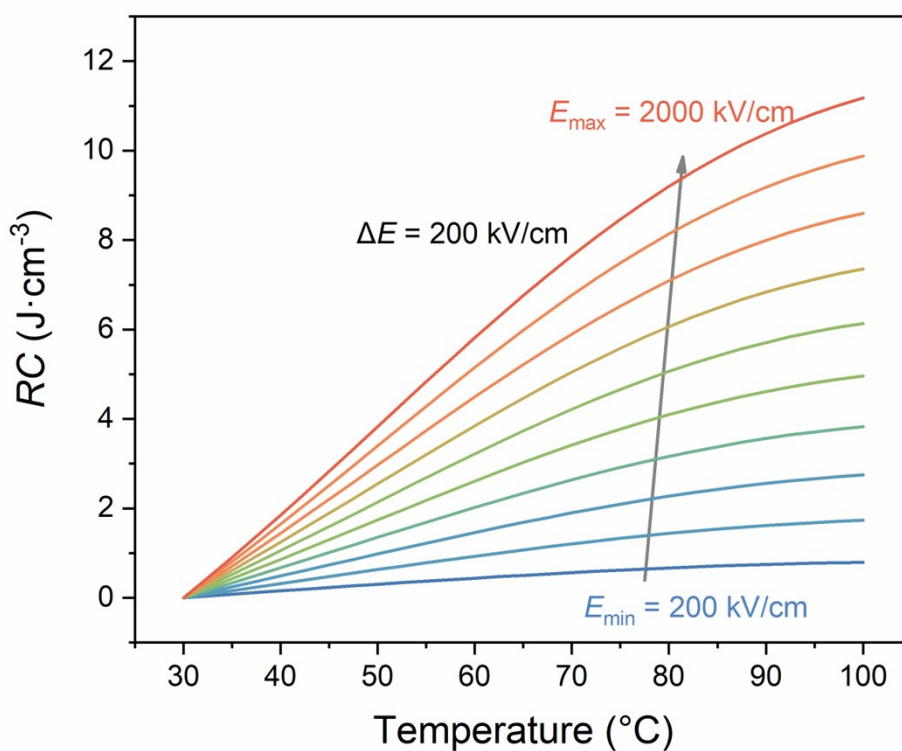


Fig. S7. Refrigerant capacity of the PLZT 6/80/20 thin film at different electric field.

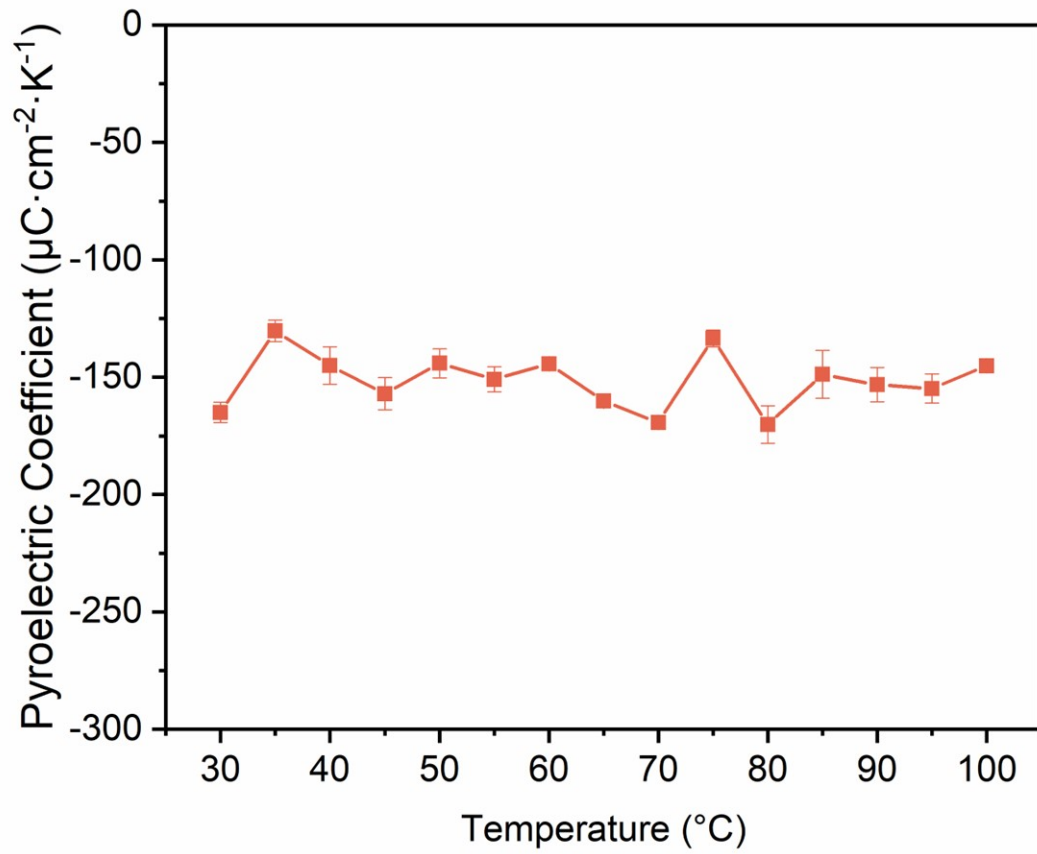


Fig. S8. The pyroelectric coefficient of the PLZT 6/80/20 thin film within the temperature range of 30 ~ 100 °C.